BC237B

Amplifier Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	45	Vdc
Collector - Emitter Voltage	V _{CES}	50	Vdc
Collector - Emitter Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	100	mAdc
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	350 2.8	mW mW/°C
Total Power Dissipation @ T _A = 25°C Derate above T _A = 25°C	P _D	1.0 8.0	W mW/°C
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

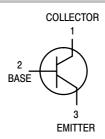
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	125	°C/W

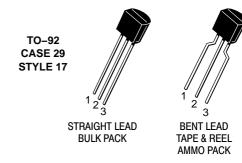
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



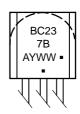
ON Semiconductor®

http://onsemi.com





MARKING DIAGRAM



= Assembly Location

= Year WW = Work Week = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC237B	TO-92	5000 Units / Bulk
BC237BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC237BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

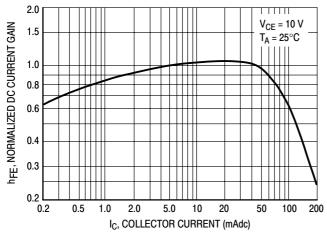
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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	1 - 3		<u> </u>	I	1
Collector – Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	45	-	_	V
Emitter – Base Breakdown Voltage ($I_E = 100 \mu A$, $I_C = 0$)	V _{(BR)EBO}	6.0	_	-	V
Collector Cutoff Current $(V_{CE} = 50 \text{ V}, V_{BE} = 0)$ $(V_{CE} = 50 \text{ V}, V_{BE} = 0) \text{ T}_{A} = 125^{\circ}\text{C}$	I _{CES}	_ _	0.2 0.2	15 4.0	nA μA
ON CHARACTERISTICS	·				
DC Current Gain (I _C = 10 μ A, V _{CE} = 5.0 V)	h _{FE}	_	150	-	-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$		200	290	460	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$		_	180	_	
Collector – Emitter On Voltage ($I_C = 10 \text{ mA}$, $I_B = 0.5 \text{ mA}$) ($I_C = 100 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	V _{CE(sat)}	_ _	0.07 0.2	0.2 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)	V _{BE(sat)}	- -	0.6	0.83 1.05	V
Base–Emitter On Voltage ($I_C = 100 \mu A, V_{CE} = 5.0 V$) ($I_C = 2.0 mA, V_{CE} = 5.0 V$) ($I_C = 100 mA, V_{CE} = 5.0 V$)	V _{BE(on)}	_ 0.55 _	0.5 0.62 0.83	- 0.7 -	V
DYNAMIC CHARACTERISTICS					
Current – Gain — Bandwidth Product ($I_C = 0.5 \text{ mA}$, $V_{CE} = 3.0 \text{ V}$, $f = 100 \text{ MHz}$) ($I_C = 10 \text{ mA}$, $V_{CE} = 5.0 \text{ V}$, $f = 100 \text{ MHz}$)	f _T	_ 150	100 200	_ _	MHz
Collector–Base Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)	C _{obo}	-	-	4.5	pF
Emitter–Base Capacitance ($V_{EB} = 0.5 \text{ V}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	C _{ibo}	_	8.0	-	pF
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2.0 k Ω , f = 1.0 kHz, Δ f = 200 Hz)	NF	_	2.0	10	dB

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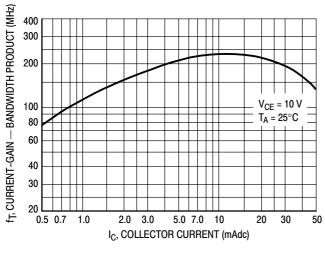
1.0



T_A = 25°C 0.9 0.8 $V_{BE(sat)} @ I_C/I_B = 10$ 0.7 V, VOLTAGE (VOLTS) V_{BE(on)} @ V_{CE} = 10 V 0.6 0.5 0.3 0.2 $V_{CE(sat)} @ I_C/I_B = 10$ 0.1 0.2 0.3 0.5 0.7 1.0 2.0 3.0 5.07.010 20 30 50 70 100 0.1 IC, COLLECTOR CURRENT (mAdc)

Figure 1. Normalized DC Current Gain

Figure 2. "Saturation" and "On" Voltages



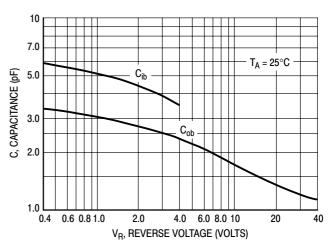


Figure 3. Current-Gain — Bandwidth Product

Figure 4. Capacitances

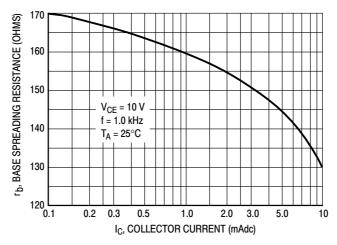
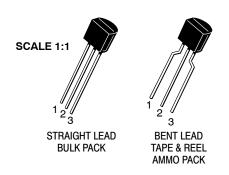


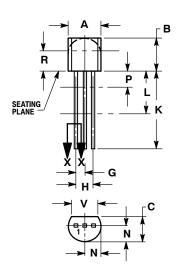
Figure 5. Base Spreading Resistance





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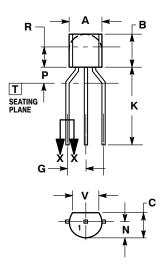


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INC	HES	MILLIN	IETERS
DIM	MIN MAX		MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS					
DIM	MIN MAX					
Α	4.45	5.20				
В	4.32	5.33				
С	3.18	4.19				
D	0.40	0.54				
G	2.40	2.80				
J	0.39	0.50				
K	12.70					
N	2.04	2.66				
P	1.50	4.00				
R	2.93					
٧	3.43					

STYLES ON PAGE 2

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STYLE 1: PIN 1. 2. 3.	EMITTER BASE COLLECTOR	STYLE 2: PIN 1. 2. 3.	BASE EMITTER COLLECTOR	STYLE 3: PIN 1. 2. 3.	ANODE ANODE CATHODE	STYLE 4: PIN 1. 2. 3.	CATHODE CATHODE ANODE	STYLE 5: PIN 1. 2. 3.	DRAIN SOURCE GATE
2. 3.	SOURCE & SUBSTRATE DRAIN	2. 3.	DRAIN GATE	2. 3.	GATE SOURCE & SUBSTRATE	2. 3.	EMITTER BASE 2	2. 3.	ANODE
2.	ANODE CATHODE & ANODE CATHODE	STYLE 12: PIN 1. 2. 3.	MAIN TERMINAL 1 GATE MAIN TERMINAL 2	STYLE 13: PIN 1. 2. 3.	ANODE 1 GATE CATHODE 2	STYLE 14: PIN 1. 2. 3.	EMITTER COLLECTOR BASE	STYLE 15: PIN 1. 2. 3.	ANODE 1 CATHODE ANODE 2
STYLE 16: PIN 1. 2. 3.	ANODE GATE CATHODE	STYLE 17: PIN 1. 2. 3.	COLLECTOR BASE EMITTER	STYLE 18: PIN 1. 2. 3.	ANODE CATHODE NOT CONNECTED	STYLE 19: PIN 1. 2. 3.	GATE ANODE CATHODE	STYLE 20: PIN 1. 2. 3.	NOT CONNECTED CATHODE ANODE
2.	COLLECTOR EMITTER BASE	STYLE 22: PIN 1. 2. 3.	GATE	2	GATE SOURCE DRAIN	PIN 1. 2.	EMITTER COLLECTOR/ANODE CATHODE	PIN 1.	MT 1 GATE
	V _{CC} GROUND 2 OUTPUT	STYLE 27: PIN 1. 2. 3.	MT SUBSTRATE MT	STYLE 28: PIN 1. 2. 3.	CATHODE ANODE GATE	STYLE 29: PIN 1. 2. 3.	NOT CONNECTED ANODE CATHODE	STYLE 30: PIN 1. 2. 3.	DRAIN GATE SOURCE
	GATE	PIN 1. 2.	BASE COLLECTOR EMITTER	PIN 1.	RETURN INPUT	2.	INPUT GROUND LOGIC	2.	

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DOCUMENT	NUMBER:
98ASB42022	В

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